

EAST - [3239.wsp:1]

FileViewEditToolsWindowHelp

Active

L6: (6331) ((fer\$10 "FeRAM") near3 capacitor)

L7: (6331) ((fer\$10 "FeRAM") near3 capacitor) 6 and (electrode plate)

L8: (3545) 7 and dielectric

L9: (1534) 8 and barrier

L10: (1155) 9 and oxygen

L11: (201) 10 and (seed liner lining)

L12: (197) 11 and ((top bottom first second lower upper) near4 (electrode plate))

L13: (133) 12 and ((top bottom first second lower upper) near4 (barrier))

L14: (65) 13 and (glue adhes\$4)

Failed

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QEsUS:PGPHB;USPAT:EPD;IPO

Default operator:OR

13 and (glue adhes\$4)

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	U	Document I	Issue Dat	Page	Title	Current O	Current X	Retrieval	Inventor	S	C	P	2	3	6
1	r	US 2004023	2004112	14	MEMORY ARCHITECT	257/295			Wohlfahrt, Joerg et	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	r	US 2004020	2004102	22	Low temperature chemica	438/3	438/240;		Hintermaier, Frank	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	r	US 2004016	2004082	66	Manufacturing method of	438/3	257/E21.0		Sashida, Naoya et al	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	r	US 2004015	2004080	10	FERROELECTRIC ME	257/306	257/310;		Lee, Kyu-Mann	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	r	US 2004007	2004041	13	Ferroelectric capacitor m	438/396			Lung, Hsiang-Lan	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	r	US 2004007	2004041	14	Ferroelectric device and	257/295	257/E21.0		Lung, Hsiang-Lan	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	r	US 2004005	2004032	13	SERIES MEMORY ARC	257/295			Wohlfahrt, Joerg	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
8	r	US 2004005	2004032	13	MEMORY ARCHITECT	257/295	257/E21.6		Jacob, Michael et al	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
9	r	US 2004004	2004031	47	Semiconductor device an	257/200			Sashida, Naoya	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
10	r	US 2003023	2003122	15	Memory integrated circui	713/322			Jacob, Michael	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
11	r	US 2003022	2003120	17	Ferroelectric memory inte	257/200	257/E21.6		Jacob, Michael et al	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
12	r	US 2003021	2003112	20	Ferroelectric capacitor, m	257/295	257/306;		Hase, Takashi	<input checked="" type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

FileDetailsHTML

Ready

~~3~~ Failed

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 PDF form
  ISIR form
  Image
  Text
  HTML

	U	D	I	S	P	T	C	X	R	I	I	S	C	P	2	3	4	5
24	r	r	US 6872995	2005032	19	Ferroelectric capacitor, m	257/295	257/310;		Hase; Takashi	f	r	r	r	r	r	r	r
25	r	c	US 6858890	2005022	16	Ferroelectric memory inte	257/296	257/303;		Jacob; Michael et al	f	r	r	r	r	r	r	r
26	r	r	US 6800890	2004100	13	Memory architecture wit	257/295	257/200;		Wohlfahrt; Joerg et	f	r	r	r	r	r	r	r
27	r	r	US 6798010	2004092	9	Ferroelectric memory dev	257/310	257/532;		Lee; Kyu-Mann	f	r	r	r	r	r	r	r
28	r	r	US 6795329	2004092	15	Memory integrated circui	365/145	365/149		Jacob; Michael	f	r	r	r	r	r	r	r
29	r	c	US 6764862	2004072	16	Method of forming ferroe	438/3	438/238;		Park; Kun-Sang et a	f	r	r	r	r	r	r	r
30	r	r	US 6730523	2004050	23	Low temperature chemica	438/3	257/E21.2		Hintennaier; Frank	f	r	r	r	r	r	r	r
31	r	r	US 6724026	2004042	13	Memory architecture wit	257/295	257/296;		Jacob; Michael et al	f	r	r	r	r	r	r	r
32	r	r	US 6720598	2004041	13	Series memory architectu	257/295	257/296;		Wohlfahrt; Joerg	f	r	r	r	r	r	r	r
33	r	r	US 6708405	2004032	15	Method for producing an	29/852	216/18;		Hasler; Barbara et a	f	r	r	r	r	r	r	r
34	r	r	US 6699725	2004030	10	Methods of fabricating fe	438/3	257/E21.0		Lee; Kyu-Mann	f	r	r	r	r	r	r	r
35	r	r	US 6635528	2003102	22	Method of planarizing a c	438/253	257/E21.3		Gilbert; Stephen R.	f	r	r	r	r	r	r	r
36	r	r	US 6611449	2003082	11	Contact for memory cells	365/145	257/E21.6		Hilliger; Andreas	f	r	r	r	r	r	r	r
37	r	c	US 6600183	2003072	20	Integrated circuit capacit	257/295	257/310;		Visokay; Mark R. et	f	r	r	r	r	r	r	r
38	r	r	US 6576546	2003061	21	Method of enhancing adh	438/629	257/E21.2		Gilbert; Stephen R.	f	r	r	r	r	r	r	r
39	r	r	US 6555431	2003042	20	Method for forming integ	438/253	257/E21.0		Xing; Guoqiang et a	f	r	r	r	r	r	r	r
40	r	r	US 6538272	2003032	15	Semiconductor storage de	257/295	257/303;		Yamazaki; Shinobu	f	r	r	r	r	r	r	r
41	r	c	US 6534809	2003031	22	Hardmask designs for dry	257/295	257/751;		Moise; Theodore et	f	r	r	r	r	r	r	r
42	r	r	US 6444542	2002090	42	Integrated circuit and met	438/448	257/E21.0		Moise; Theodore S.	f	r	r	r	r	r	r	r
43	r	r	US 6350643	2002022	16	Reduced degradation of	438/240	257/E21.2		Hintennaier; Frank	f	r	r	r	r	r	r	r
44	r	r	US 6344413	2002020	15	Method for forming a se	438/678	438/240;		Zurcher; Peter et al.	f	r	r	r	r	r	r	r

